

The resulting quiescent point from Fig. 7.59 is given by

$$I_{DQ} = 3.4 \text{ mA}$$

$$V_{GSQ} = 1.4 \text{ V}$$

For V_{DS} , Kirchhoff's voltage law results in

$$-I_D R_S + V_{DS} - I_D R_D + V_{DD} = 0$$

and

$$V_{DS} = -V_{DD} + I_D(R_D + R_S)$$

$$= -20 \text{ V} + (3.4 \text{ mA})(2.7 \text{ k}\Omega + 1.8 \text{ k}\Omega)$$

$$= -20 \text{ V} + 15.3 \text{ V}$$

$$= -4.7 \text{ V}$$

7.14 UNIVERSAL JFET BIAS CURVE

Since the dc solution of a FET configuration requires drawing the transfer curve analysis, a universal curve was developed that can be used for any level of I_{DSS} and universal curve for an n -channel JFET or depletion-type MOSFET (for negative V_{GSQ}) is provided in Fig. 7.60. Note that the horizontal axis is not that of V_{GS} normalized level defined by $V_{GS}/|V_P|$, the $|V_P|$ indicating that only the magnitude of V_P is to be employed, not its sign. For the vertical axis, the scale is also a normalized level of I_D/I_{DSS} . The result is that when $I_D = I_{DSS}$, the ratio is 1, and when $V_{GS} = V_P$, the ratio $V_{GS}/|V_P| = -1$. Note also that the scale for I_D/I_{DSS} is on the left rather than on the right as encountered for I_D in past exercises. The additional two scales on the right need an introduction. The vertical scale labeled m can in itself be used to find the solution to fixed-bias configurations. The other scale, labeled M , is employed along with the m scale to find the solution to divider configurations. The scaling for m and M come from a mathematical derivation.

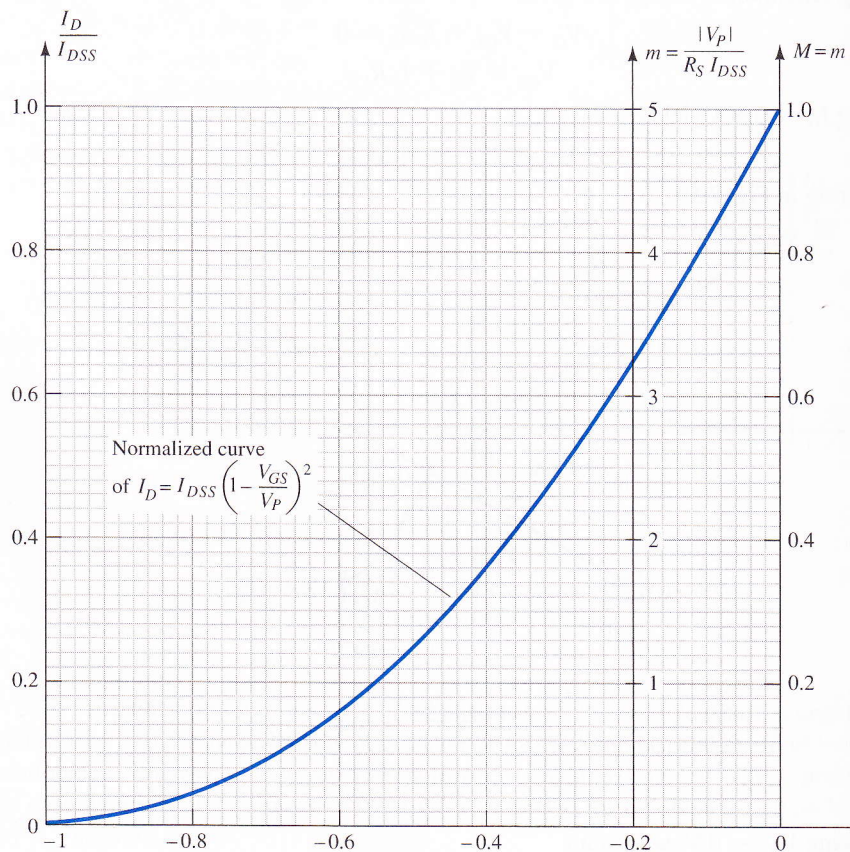


FIG. 7.60

Universal JFET bias curve.